Inducing a Finite In-Plane Piezoelectricity in Graphene with Low Concentration of Inversion Symmetry-breaking Defects.

Khaled E. El-Kelany,^{a,b} Philippe Carbonnière,^a Alessandro Erba,^c and Michel Rérat^a

^a Equipe de Chimie Physique, IPREM UMR5254, Université de Pau et des Pays de l'Adour, 64000 Pau, France

^b Chemistry Department, Faculty of Science, Minia University, Minia 61519, Egypt

^c Dipartimento di Chimica and Centre of Excellence NIS (Nanostructured Interfaces and Surfaces), Universit`a di Torino, via Giuria 5, IT-10125 Torino, Italy

e-mail: khaled.el-kelany@univ-pau.fr

In this work¹, we adopt a quantum mechanical approach based on the periodic Density Functional Theory (DFT), to show that a finite in-plane piezoelectricity can be induced in graphene by breaking its inversion center with any in-plane defect, in the limit of vanishing defect concentration. We first consider different patterns of BN-doped graphene sheets of D3h symmetry, whose electronic and piezoelectric (dominated by the electronic rather than nuclear term) properties are characterized at the *ab initio* level of theory. We then consider other in-plane defects, such as holes of D3h or C2v point-symmetry, and confirm that a common limit value (for low defect concentration) of the piezoelectric response of graphene is obtained regardless of the particular chemical or physical nature

of the defects ($e_{11} \approx 4.5 \ 10^{-10} \text{ C/m}$ and $d_{11} \approx 1.5 \text{ pm/V}$ for direct and converse piezoelectricity, respectively). This in-plane piezoelectric response of graphene is one-order of magnitude larger than the out-of plane previously investigated one². All the calculations are performed using the CRYSTAL14 program³.



- 1. Kh. E. El-kelany, Ph. Carbonnière, A. Erba, and M. Rérat, J. Phys. Chem. C 2015, (submitted).
- 2. M. T. Ong and E. J. Reed, ACS Nano 2012, 6, 1387-1394.
- R. Dovesi, R. Orlando, A. Erba, C. M. Zicovich-Wilson, B. Civalleri, S. Casassa, L. Maschio, M. Ferrabone, M. De La Pierre, Ph. D'Arco, et al., *Int. J. Quantum Chem.* 2014, 114, 1287-1317.